

4V Drive Nch + Pch MOSFET

QS8M11

● Structure

Silicon N-channel MOSFET/
 Silicon P-channel MOSFET

● Features

- 1) Low on-resistance.
- 2) High power package(TSMT8).
- 3) Low voltage drive(4V drive).

● Application

Switching

● Packaging specifications

Type	Package	Taping
	Code	TR
	Basic ordering unit (pieces)	3000
QS8M11		○

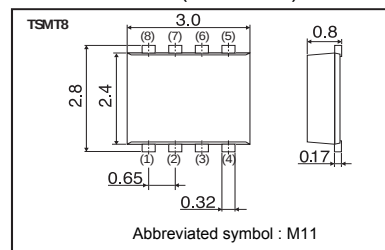
● Absolute maximum ratings (Ta = 25°C)

Parameter	Symbol	Limits		Unit
		Tr1 : N-ch	Tr2 : P-ch	
Drain-source voltage	V_{DSS}	30	-30	V
Gate-source voltage	V_{GSS}	±20	±20	V
Drain current	Continuous	I_D	±3.5	A
	Pulsed	I_{DP} *1	±12	A
Source current (Body Diode)	Continuous	I_S	1.0	A
	Pulsed	I_{sp} *1	12	A
Power dissipation	P_D *2	1.5		W / TOTAL
		1.25		W / ELEMENT
Channel temperature	T_{ch}	150		°C
Range of storage temperature	T_{stg}	-55 to +150		°C

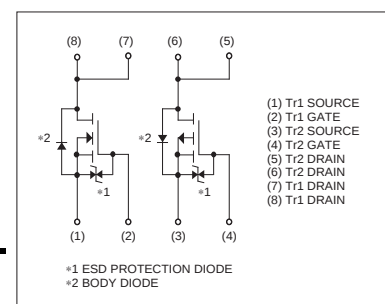
*1 $P_w \leq 10W$, Duty cycle ≤ 1%

*2 Mounted on a ceramic board.

● Dimensions (Unit : mm)



● Inner circuit



● **Electrical characteristics** (Ta = 25°C)

<Tr1(Nch)>

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Gate-source leakage	I_{GSS}	-	-	± 10	μA	$V_{GS} = \pm 20V, V_{DS} = 0V$
Drain-source breakdown voltage	$V_{(BR)DSS}$	30	-	-	V	$I_D = 1mA, V_{GS} = 0V$
Zero gate voltage drain current	I_{DSS}	-	-	1	μA	$V_{DS} = 30V, V_{GS} = 0V$
Gate threshold voltage	$V_{GS(th)}$	1.0	-	2.5	V	$V_{DS} = 10V, I_D = 1mA$
Static drain-source on-state resistance	$R_{DS(on)}^*$	-	35	50	m Ω	$I_D = 3.5A, V_{GS} = 10V$
		-	45	65		$I_D = 3.5A, V_{GS} = 4.5V$
		-	50	70		$I_D = 3.5A, V_{GS} = 4V$
Forward transfer admittance	$ Y_{fs} $	2.2	-	-	S	$V_{DS} = 10V, I_D = 3.5A$
Input capacitance	C_{iss}	-	180	-	pF	$V_{DS} = 10V$
Output capacitance	C_{oss}	-	70	-	pF	$V_{GS} = 0V$
Reverse transfer capacitance	C_{rss}	-	35	-	pF	$f = 1MHz$
Turn-on delay time	$t_{d(on)}$	-	10	-	ns	$I_D = 1.7A, V_{DD} = 15V$
Rise time	t_r	-	25	-	ns	$V_{GS} = 10V$
Turn-off delay time	$t_{d(off)}$	-	25	-	ns	$R_L = 8.8\Omega$
Fall time	t_f	-	7	-	ns	$R_G = 10\Omega$
Total gate charge	Q_g	-	3.5	-	nC	$I_D = 3.5A, V_{DD} = 15V$
Gate-source charge	Q_{gs}	-	1.0	-	nC	$V_{GS} = 5V$
Gate-drain charge	Q_{gd}	-	1.0	-	nC	

*Pulsed

● **Body diode characteristics** (Source-Drain) (Ta = 25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Forward Voltage	V_{SD}^*	-	-	1.2	V	$I_S = 3.5A, V_{GS} = 0V$

*Pulsed

● **Electrical characteristics** (Ta = 25°C)

<Tr2(Pch)>

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Gate-source leakage	I_{GSS}	-	-	± 10	μA	$V_{GS} = \pm 20V, V_{DS} = 0V$
Drain-source breakdown voltage	$V_{(BR)DSS}$	-30	-	-	V	$I_D = -1mA, V_{GS} = 0V$
Zero gate voltage drain current	I_{DSS}		-	-1	μA	$V_{DS} = -30V, V_{GS} = 0V$
Gate threshold voltage	$V_{GS(th)}$	-1.0	-	-2.5	V	$V_{DS} = -10V, I_D = -1mA$
Static drain-source on-state resistance	$R_{DS(on)}^*$	-	55	75	m Ω	$I_D = -3A, V_{GS} = -10V$
		-	85	115		$I_D = -1.5A, V_{GS} = -4.5V$
		-	95	125		$I_D = -1.5A, V_{GS} = -4.0V$
Forward transfer admittance	$ Y_{fs} ^*$	2.4	-	-	S	$V_{DS} = -10V, I_D = -3A$
Input capacitance	C_{iss}	-	480	-	pF	$V_{DS} = -10V$
Output capacitance	C_{oss}	-	70	-	pF	$V_{GS} = 0V$
Reverse transfer capacitance	C_{rss}	-	70	-	pF	$f = 1MHz$
Turn-on delay time	$t_{d(on)}^*$	-	7	-	ns	$I_D = -1.5A, V_{DS} = -15V$
Rise time	t_r^*	-	18	-	ns	$V_{GS} = -10V$
Turn-off delay time	$t_{d(off)}^*$	-	50	-	ns	$R_L = 10\Omega$
Fall time	t_f^*	-	35	-	ns	$R_G = 10\Omega$
Total gate charge	Q_g^*	-	5.2	-	nC	$I_D = -3A, V_{DD} = -15V$
Gate-source charge	Q_{gs}^*	-	1.6	-	nC	$V_{GS} = -5V$
Gate-drain charge	Q_{gd}^*	-	1.6	-	nC	

*Pulsed

● **Body diode characteristics** (Source-Drain) (Ta = 25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Forward Voltage	V_{SD}^*	-	-	-1.2	V	$I_s = -3A, V_{GS} = 0V$

*Pulsed

● Electrical characteristics curves

<Tr1(Nch)>

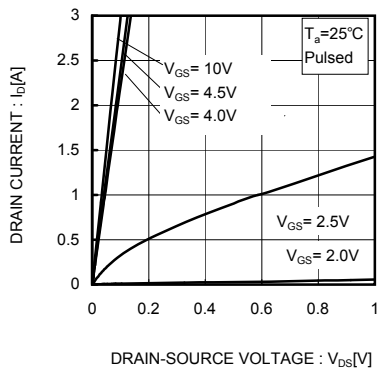


Fig.1 Typical Output Characteristics(I)

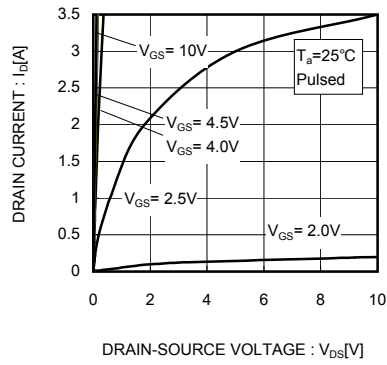


Fig.2 Typical Output Characteristics(II)

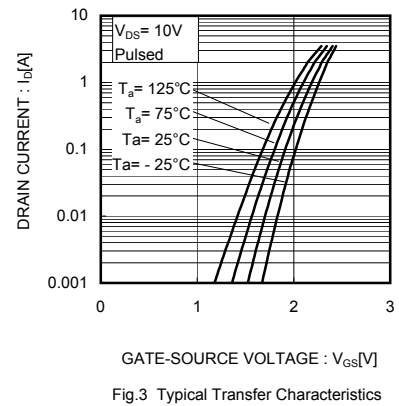


Fig.3 Typical Transfer Characteristics

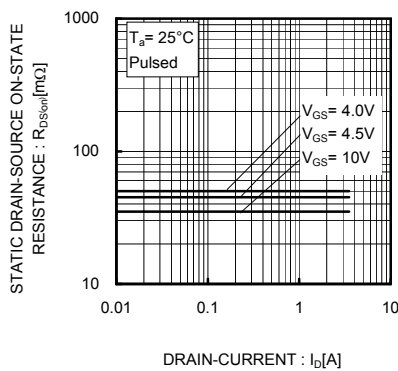


Fig.4 Static Drain-Source On-State Resistance vs. Drain Current(I)

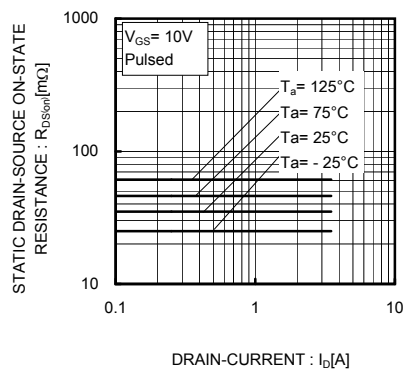


Fig.5 Static Drain-Source On-State Resistance vs. Drain Current(II)

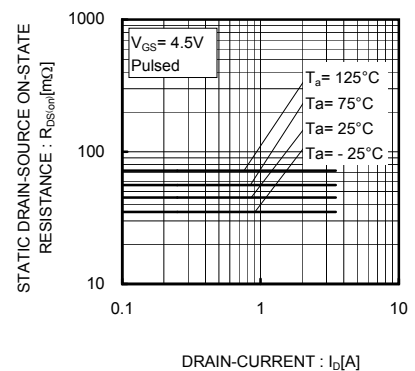


Fig.6 Static Drain-Source On-State Resistance vs. Drain Current(III)

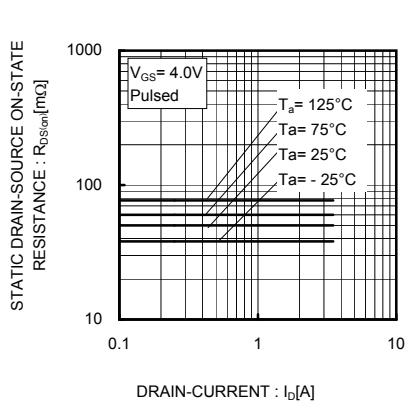


Fig.7 Static Drain-Source On-State Resistance vs. Drain Current(IV)

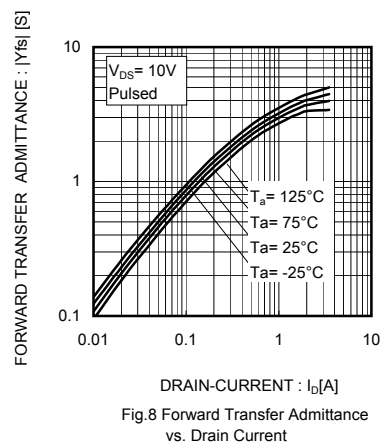


Fig.8 Forward Transfer Admittance vs. Drain Current

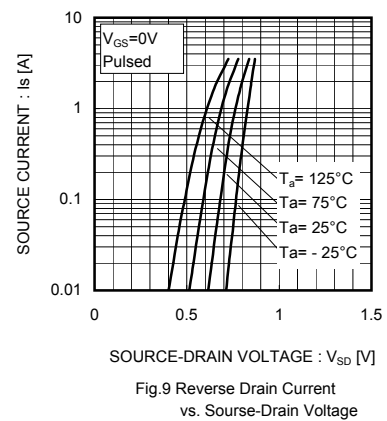


Fig.9 Reverse Drain Current vs. Source-Drain Voltage

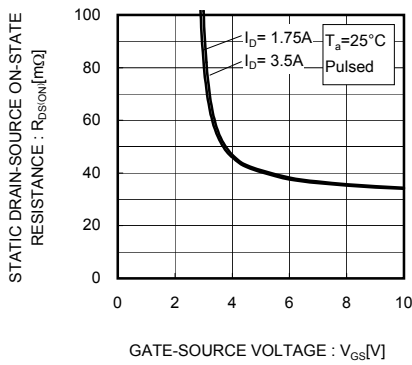


Fig.10 Static Drain-Source On-State Resistance vs. Gate Source Voltage

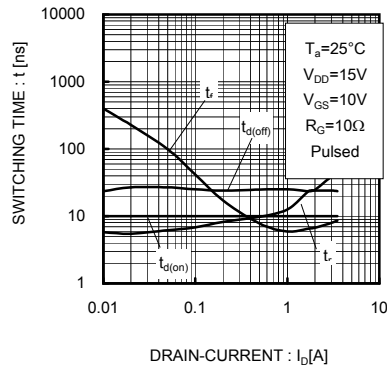


Fig.11 Switching Characteristics

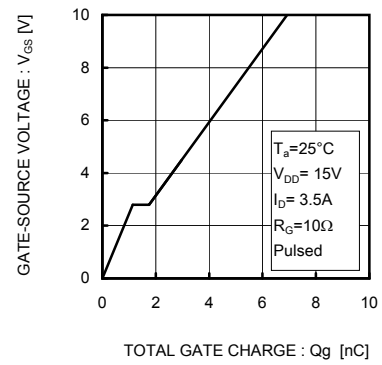


Fig.12 Dynamic Input Characteristics

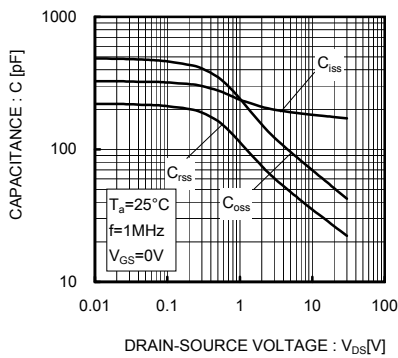


Fig.13 Typical Capacitance vs. Drain-Source Voltage

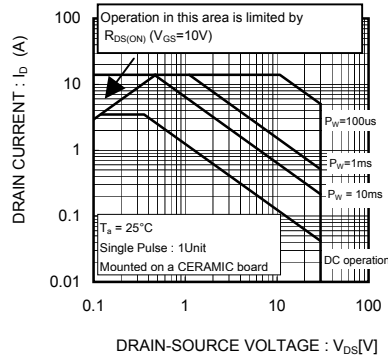


Fig.14 Maximum Safe Operating Area

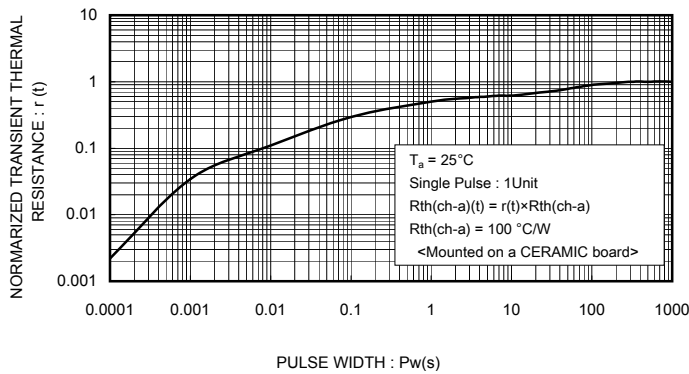


Fig.15 Normalized Transient Thermal Resistance vs. Pulse Width

● Electrical characteristics curves

<Tr2(Pch)>

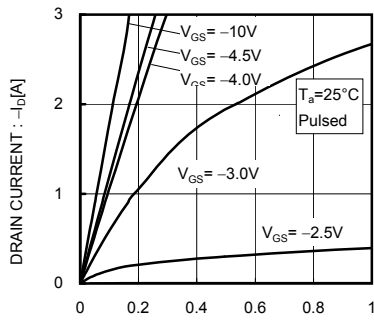


Fig.1 Typical Output Characteristics(I)

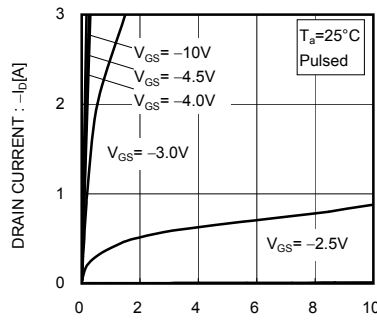


Fig.2 Typical Output Characteristics(II)

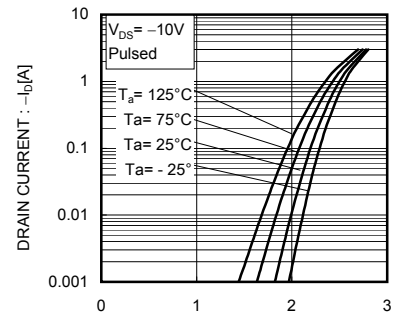


Fig.3 Typical Transfer Characteristics

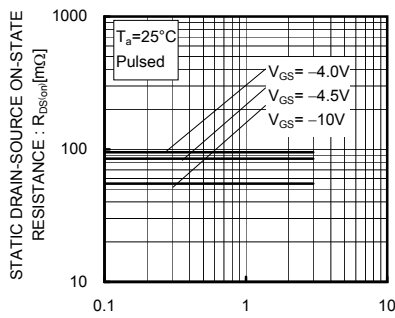


Fig.4 Static Drain-Source On-State Resistance vs. Drain Current(I)

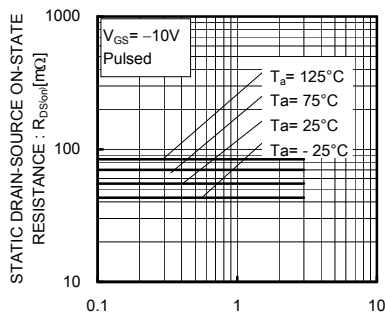


Fig.5 Static Drain-Source On-State Resistance vs. Drain Current(II)

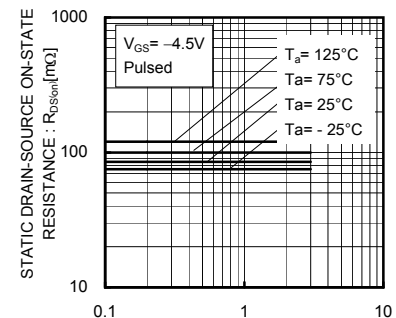


Fig.6 Static Drain-Source On-State Resistance vs. Drain Current(III)

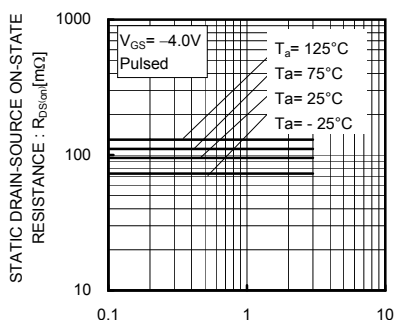


Fig.7 Static Drain-Source On-State Resistance vs. Drain Current(IV)

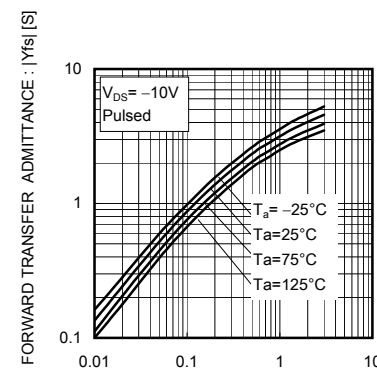


Fig.8 Forward Transfer Admittance vs. Drain Current

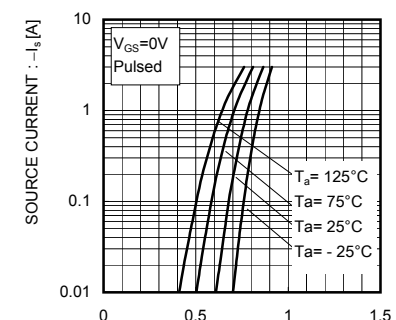


Fig.9 Reverse Drain Current vs. Source-Drain Voltage

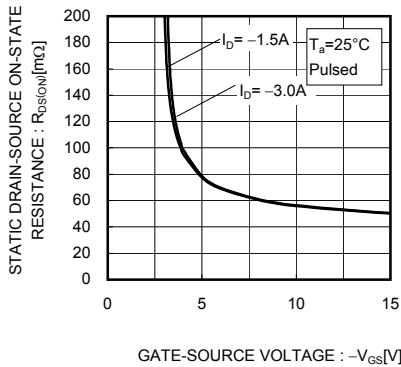


Fig.10 Static Drain-Source On-State Resistance vs. Gate Source Voltage

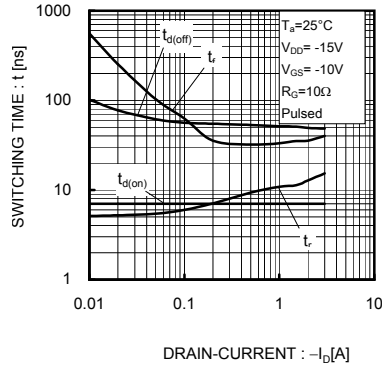


Fig.11 Switching Characteristics

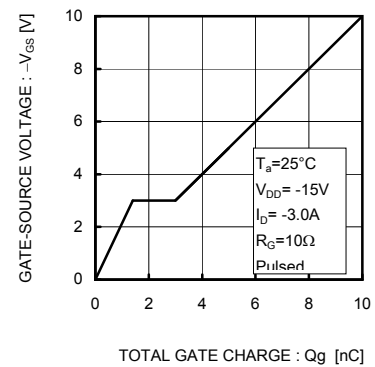


Fig.12 Dynamic Input Characteristics

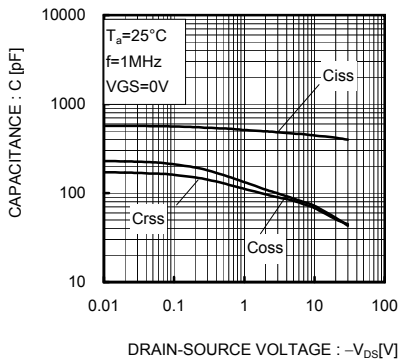


Fig.13 Typical Capacitance vs. Drain-Source Voltage

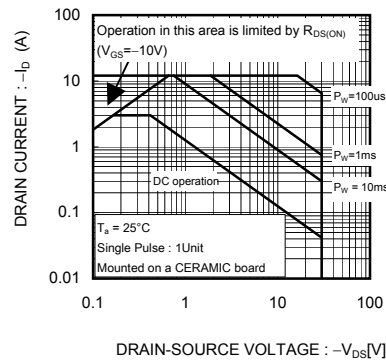


Fig.14 Maximum Safe Operating Area

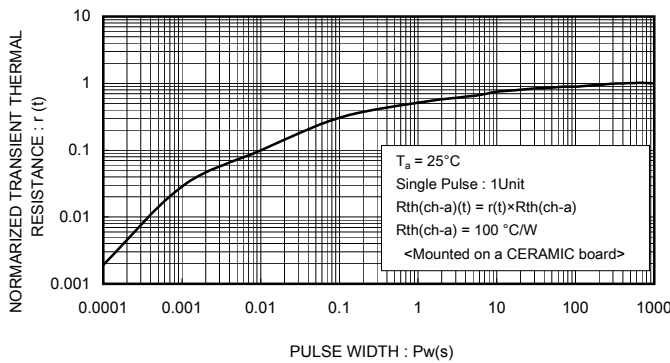


Fig.15 Normalized Transient Thermal Resistance vs. Pulse Width

● Measurement circuits

<Tr1(Nch)>

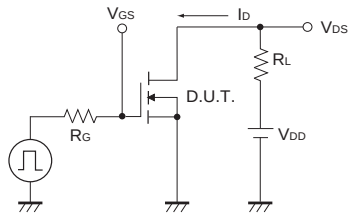


Fig.1-1 Switching Time Measurement Circuit

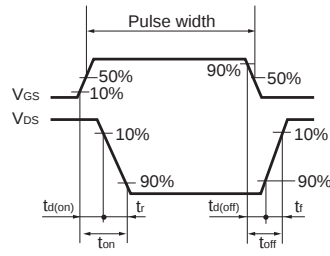


Fig.1-2 Switching Waveforms

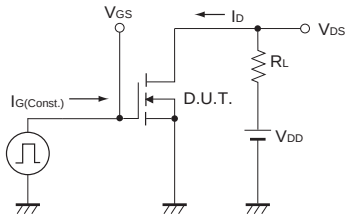


Fig.2-1 Gate Charge Measurement Circuit

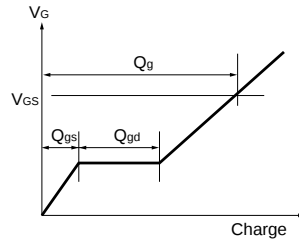


Fig.2-2 Gate Charge Waveform

<Tr2(Pch)>

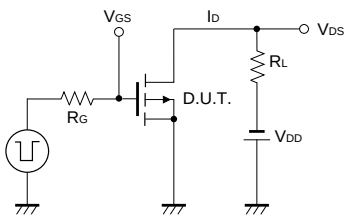


Fig.3-1 Switching Time Measurement Circuit

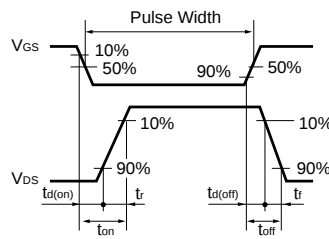


Fig.3-2 Switching Waveforms

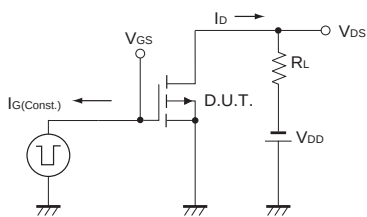


Fig.4-1 Gate Charge Measurement Circuit

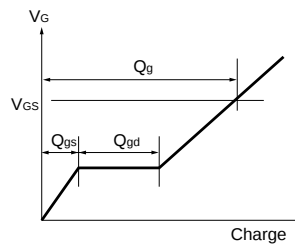


Fig.4-2 Gate Charge Waveform

● Notice

This product might cause chip aging and breakdown under the large electrified environment. Please consider to design ESD protection circuit.

Notes

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